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[SI6966DQ-T1-E3](#)

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**Si6966DQ**  
Vishay Siliconix

## Dual N-Channel 2.5-V (G-S) MOSFET

### PRODUCT SUMMARY

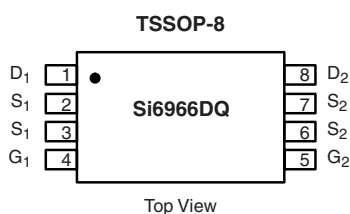
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A)
20	0.030 at $V_{GS} = 4.5$ V	4.5
	0.040 at $V_{GS} = 2.5$ V	3.9

### FEATURES

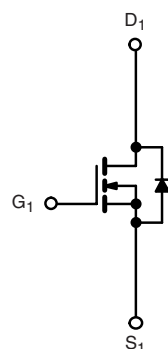
- Halogen-free Option Available
- TrenchFET® Power MOSFETs: 2.5 V Rated



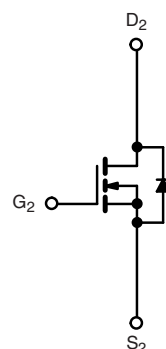
**RoHS\***  
COMPLIANT



**Ordering Information:** Si6966DQ-T1  
Si6966DQ-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



N-Channel MOSFET

### ABSOLUTE MAXIMUM RATINGS $T_A = 25^\circ\text{C}$ , unless otherwise noted

Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		$V_{DS}$	20		V
Gate-Source Voltage		$V_{GS}$	$\pm 12$		
Continuous Drain Current ( $T_J = 150\text{ }^{\circ}\text{C}$ ) <sup>a</sup>	$T_A = 25\text{ }^{\circ}\text{C}$	$I_D$	4.5	4.0	A
	$T_A = 70\text{ }^{\circ}\text{C}$		3.6	3.0	
Pulsed Drain Current		$I_{DM}$	30		
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	1.25	0.75	W
Maximum Power Dissipation <sup>a</sup>	$T_A = 25\text{ }^{\circ}\text{C}$	$P_D$	1.14	0.83	
	$T_A = 70\text{ }^{\circ}\text{C}$		0.73	0.53	
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	- 55 to 150		$^{\circ}\text{C}$

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	$R_{thJA}$	86	110	$^\circ\text{C/W}$
		124	150	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	52	65	

Notes:

a. Surface Mounted on FR4 board.

For SPICE model information via the Worldwide Web: <http://www.vishay.com/www/product/spice.htm>.

\* Pb containing terminations are not RoHS compliant, exemptions may apply.

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<b>SPECIFICATIONS</b> $T_J = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	0.6		1.4	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}$ , $V_{GS} = \pm 12\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 20\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 20\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 55\text{ }^{\circ}\text{C}$			25	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$ , $V_{GS} = 4.5\text{ V}$	30			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}$ , $I_D = 4.5\text{ A}$		0.021	0.030	$\Omega$
		$V_{GS} = 2.5\text{ V}$ , $I_D = 3.9\text{ A}$		0.030	0.040	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}$ , $I_D = 4.5\text{ A}$		20		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 1.25\text{ A}$ , $V_{GS} = 0\text{ V}$		0.65	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 10\text{ V}$ , $V_{GS} = 4.5\text{ V}$ , $I_D = 4.5\text{ A}$		11.5	20	nC
Gate-Source Charge	$Q_{gs}$			1.9		
Gate-Drain Charge	$Q_{gd}$			3.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}$ , $R_L = 10\text{ }\Omega$ $I_D \equiv 1\text{ A}$ , $V_{GEN} = 10\text{ V}$ , $R_G = 6\text{ }\Omega$		11	20	ns
Rise Time	$t_r$			9	15	
Turn-Off Delay Time	$t_{d(off)}$			36	55	
Fall Time	$t_f$			11	20	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 1.25\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		30	60	

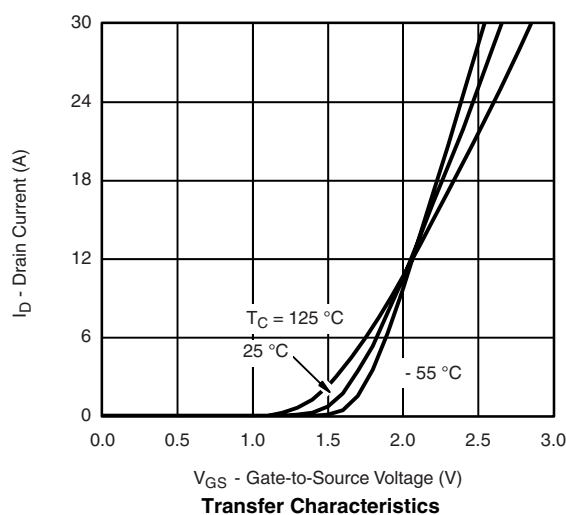
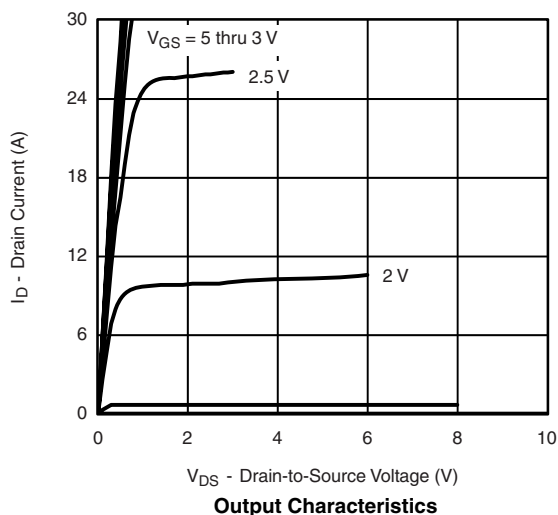
Notes:

a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .

b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS $25\text{ }^{\circ}\text{C}$ , unless otherwise noted

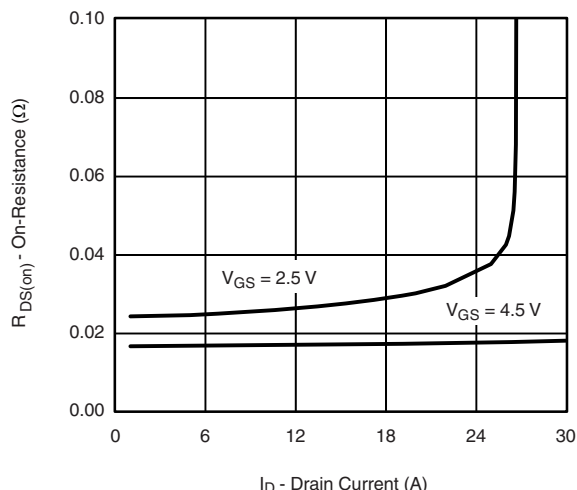




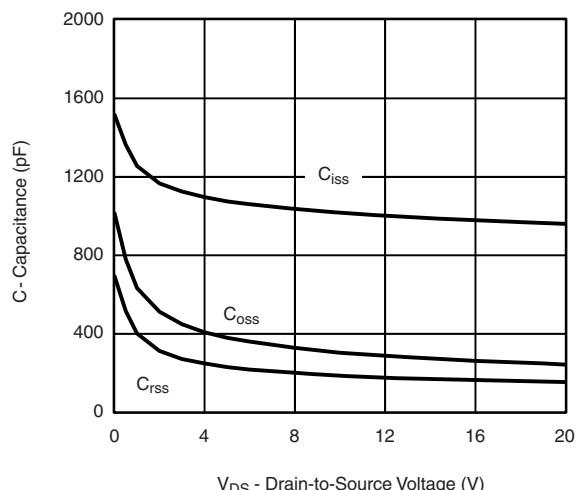
# Si6966DQ

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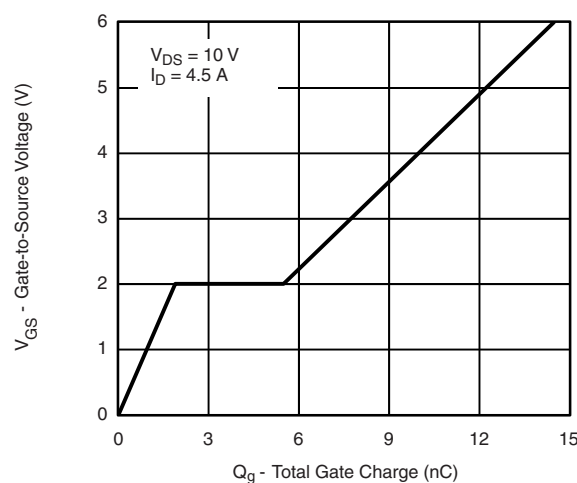
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



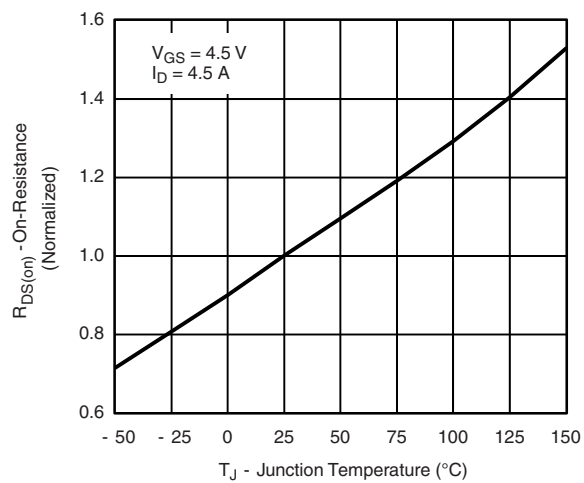
**On-Resistance vs. Drain Current**



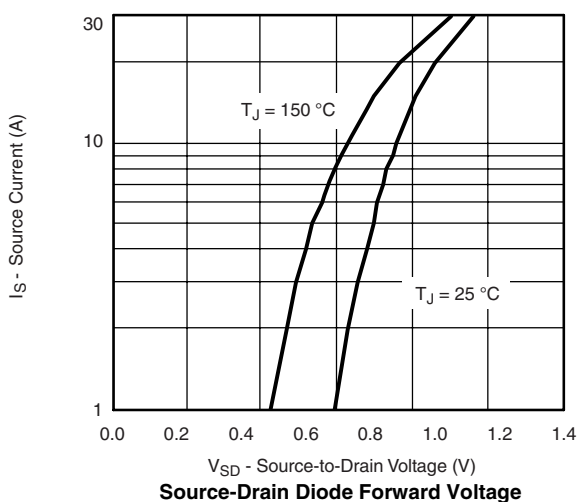
**Capacitance**



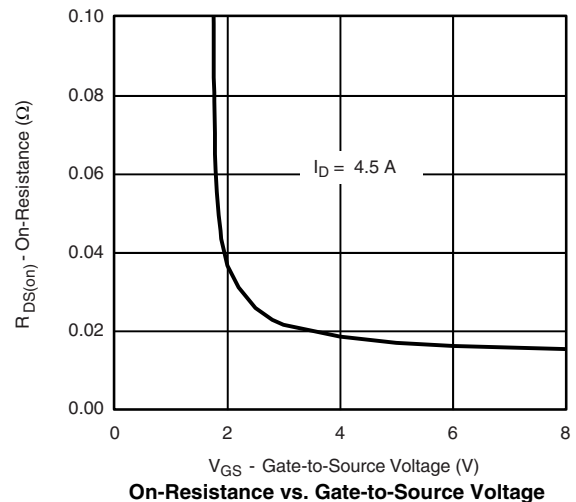
**Gate Charge**



**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**



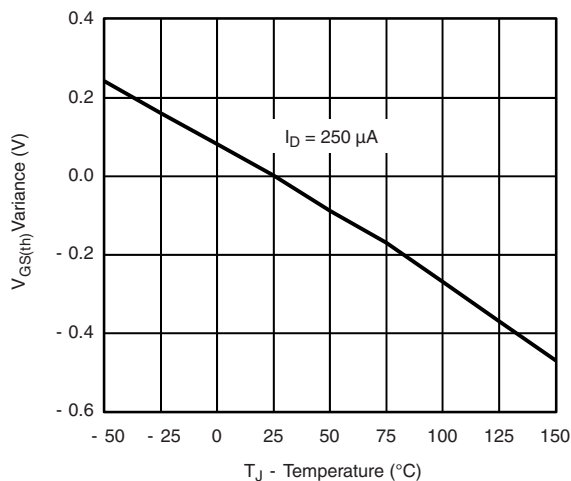
**On-Resistance vs. Gate-to-Source Voltage**

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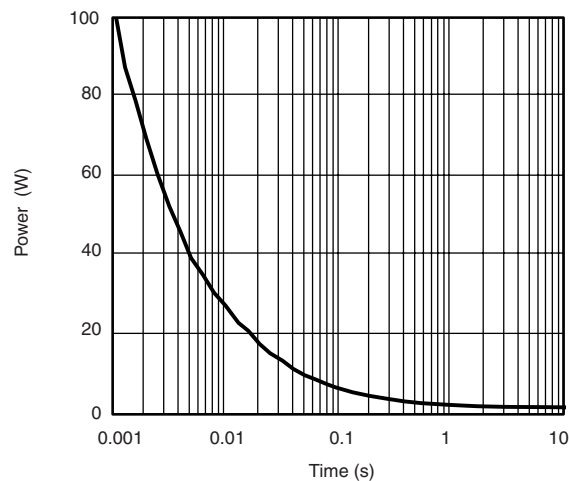
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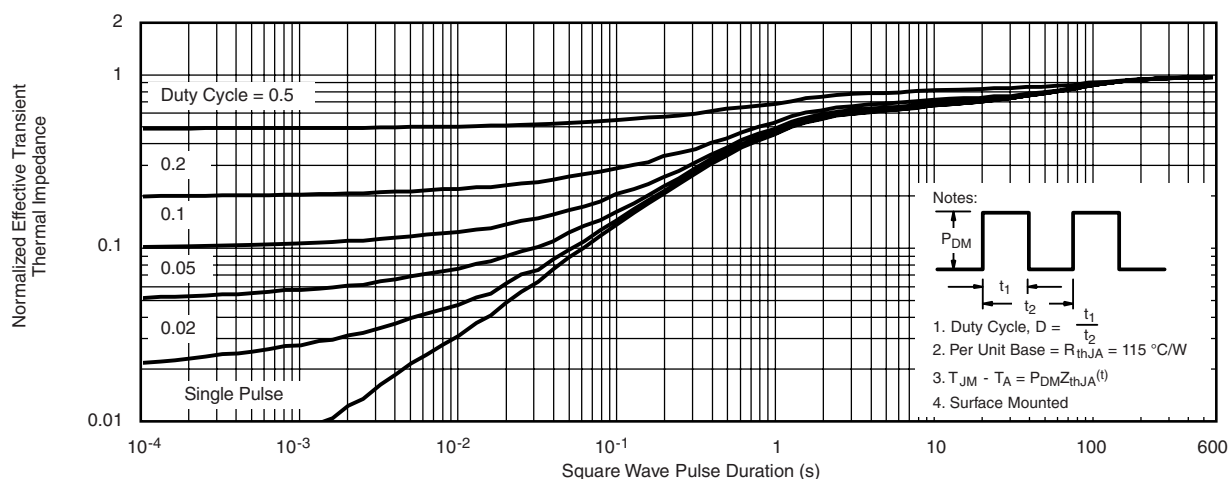
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



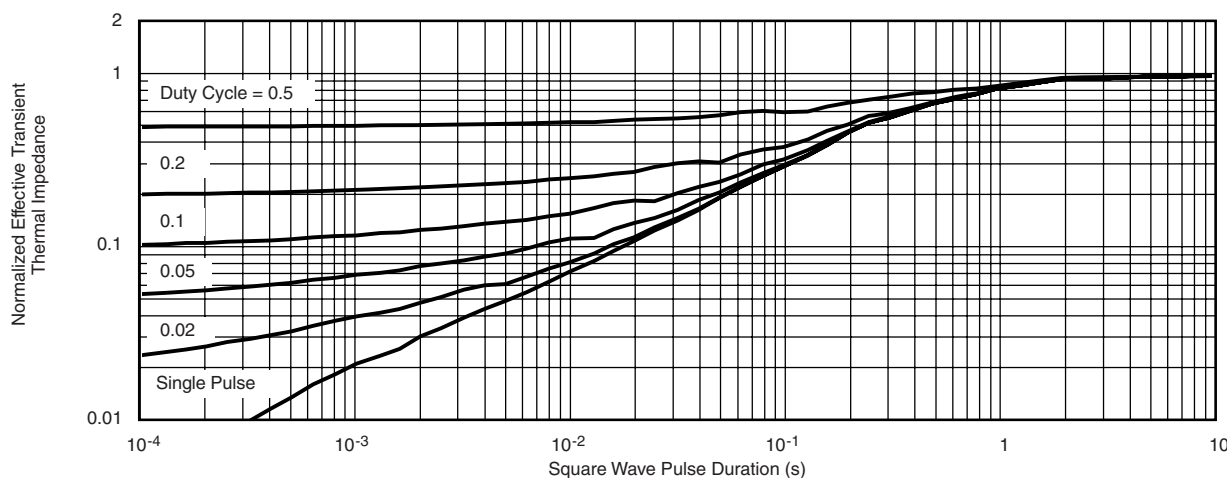
Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <http://www.vishay.com/ppg71808>.



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